

R1LV0816ASB – 5SI, 7SI

8Mb Advanced LPSRAM (512k word x 16bit)

REJ03C0387-0100

Rev.1.00

2009.12.07

Description

The R1LV0816ASB is a family of low voltage 8-Mbit static RAMs organized as 524,288-words by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies.

The R1LV0816ASB is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

The R1LV0816ASB is packaged in a 44pin thin small outline mount device [11.76mm×18.41mm 44-pin plastic TSOP (II)]. It gives the best solution for a compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

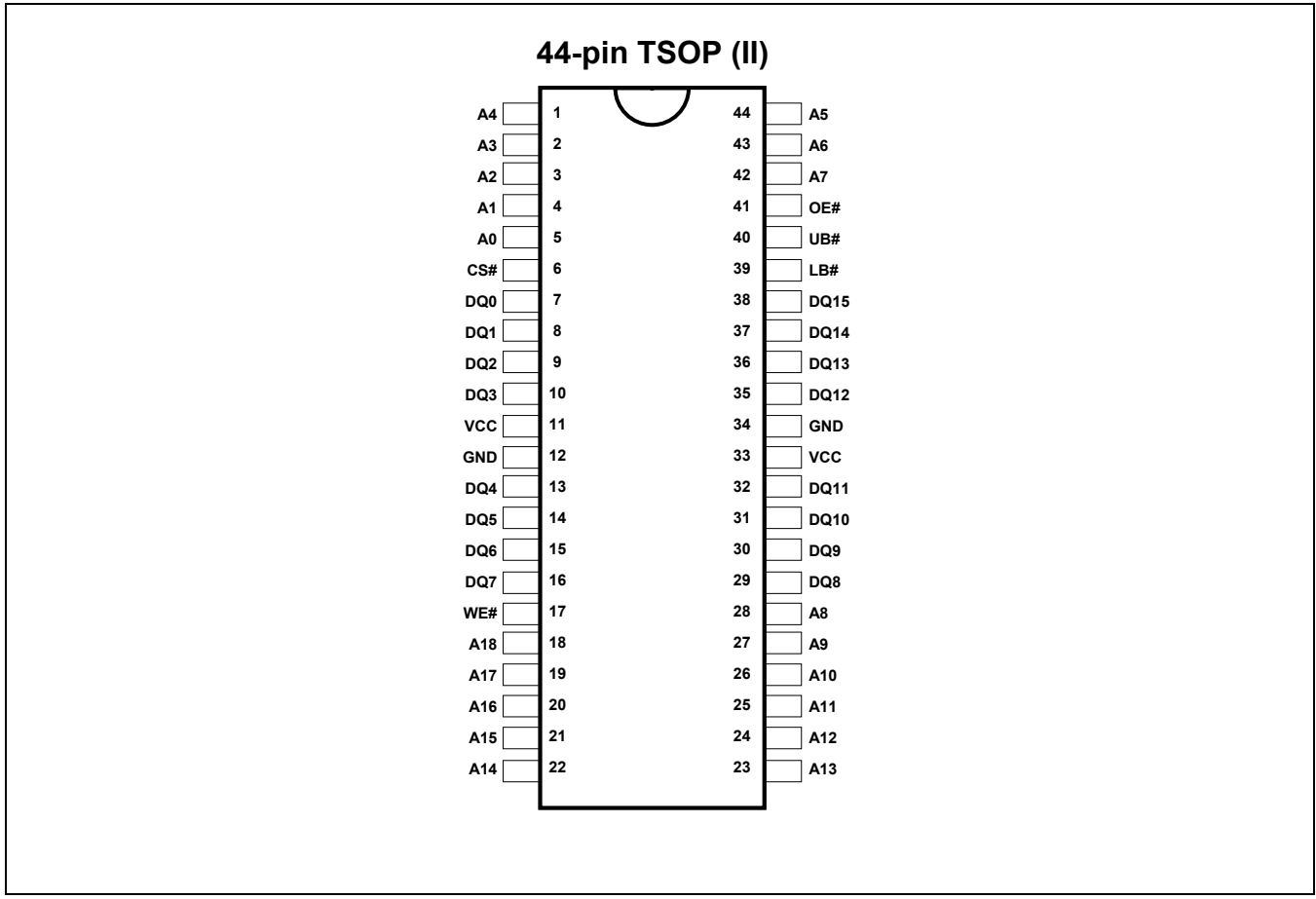
Features

- Single 2.4-3.6V power supply
- Small stand-by current: 1.2μA (Vcc=3.0V, typ.)
- No clocks, No refresh
- All inputs and outputs are TTL compatible
- Easy memory expansion by CS#, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie capability
- OE# prevents data contention in the I/O bus
- Operation temperature: -40 ~ +85°C

Ordering information

Type No.	Power supply	Access time	Temperature Range	Package
R1LV0816ASB-5SI	2.7V to 3.6V	55 ns	-40 ~ +85°C	11.76mm×18.41mm 44-pin plastic TSOP (II) (normal-bend type) (44P3F)
	2.4V to 2.7V	70 ns		
R1LV0816ASB-7SI	2.4V to 3.6V	70 ns		

Pin Arrangement



Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A18	Address input (word mode)
DQ0 to DQ15	Data input/output
CS#	Chip select
WE#	Write enable
OE#	Output enable
LB#	Lower byte enable
UB#	Upper byte enable

Operation Table

CS#	WE#	OE#	UB#	LB#	DQ0~7	DQ8~15	Operation
H	X	X	X	X	High-Z	High-Z	Stand-by
X	X	X	H	H	High-Z	High-Z	Stand-by
L	L	X	H	L	Din	High-Z	Write in lower byte
L	H	L	H	L	Dout	High-Z	Read in lower byte
L	L	X	L	H	High-Z	Din	Write in upper byte
L	H	L	L	H	High-Z	Dout	Read in upper byte
L	L	X	L	L	Din	Din	Word write
L	H	L	L	L	Dout	Dout	Word read
L	H	H	L	L	High-Z	High-Z	Output disable
L	H	H	L	H	High-Z	High-Z	Output disable
L	H	H	H	L	High-Z	High-Z	Output disable

Note 1. H: V_{IH} L: V_{IL} X: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to Vss	Vcc	-0.5 to +4.6	V
Terminal voltage on any pin relative to Vss	V_T	-0.5^{*1} to $V_{cc}+0.3^{*2}$	V
Power dissipation	P_T	0.7	W
Operation temperature	Topr	-40 to +85	°C
Storage temperature range	Tstg	-65 to 150	°C
Storage temperature range under bias	Tbias	-40 to +85	°C

Note 1. -3.0V in case of AC (Pulse width ≤ 30 ns)

2. Maximum voltage is +4.6V

Recommend Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Supply voltage	V _{CC}	2.4	3.0	3.6	V	-	
	V _{SS}	0	0	0	V	-	
Input high voltage	V _{IH}	2.0	-	V _{CC} +0.2	V	V _{CC} =2.4V to 2.7V	
		2.2	-	V _{CC} +0.2	V	V _{CC} =2.7V to 3.6V	
Input low voltage	V _{IL}	-0.2	-	0.4	V	V _{CC} =2.4V to 2.7V	1
		-0.2	-	0.6	V	V _{CC} =2.7V to 3.6V	1
Ambient temperature range	T _a	-40	-	+85	°C	-	

Note 1. -3.0V in case of AC (Pulse width ≤30ns)

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Input leakage current	I _{LI}	-	-	1	μA	V _{in} = V _{SS} to V _{CC}
Output leakage current	I _{LO}	-	-	1	μA	CS# = V _{IH} or OE# = V _{IH} or WE# = V _{IL} or LB# = UB# = V _{IH} , VI/O = V _{SS} to V _{CC}
Average operating current	I _{CC1}	-	20 ^{*1}	35	mA	Min. cycle, duty = 100%, I _{I/O} = 0mA CS# = V _{IL} , Others = V _{IH} /V _{IL}
	I _{CC2}	-	2 ^{*1}	5	mA	Cycle = 1□s, duty = 100%, I _{I/O} = 0mA CS# ≤ 0.2V, V _{IH} ≥ V _{CC} -0.2V, V _{IL} ≤ 0.2V
Standby current	I _{SB}	-	-	1	mA	CS# = V _{IH}
Standby current	I _{SB1}	-	1.2 ^{*1}	4	μA	~+25°C V _{in} ≥ 0V
		-	3 ^{*2}	6	μA	~+40°C (1) CS# ≥ V _{CC} -0.2V or (2) LB# = UB# ≥ V _{CC} -0.2V, CS# ≤ 0.2V,
		-	-	15	μA	~+70°C
		-	-	20	μA	~+85°C
Output high voltage	V _{OH}	2.4	-	-	V	I _{OH} = -1mA V _{CC} ≥ 2.7V
	V _{OH2}	2.0	-	-	V	I _{OH} = -0.1mA
Output low voltage	V _{OL}	-	-	0.4	V	I _{OL} = 2mA V _{CC} ≥ 2.7V
	V _{OL2}	-	-	0.4	V	I _{OL} = 0.1mA

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V(T_a=+25°C), and not 100% tested.

2. Typical parameter indicates the value for the center of distribution at 3.0V(T_a=+40°C), and not 100% tested.

Capacitance

(Ta =25°C, f =1MHz)

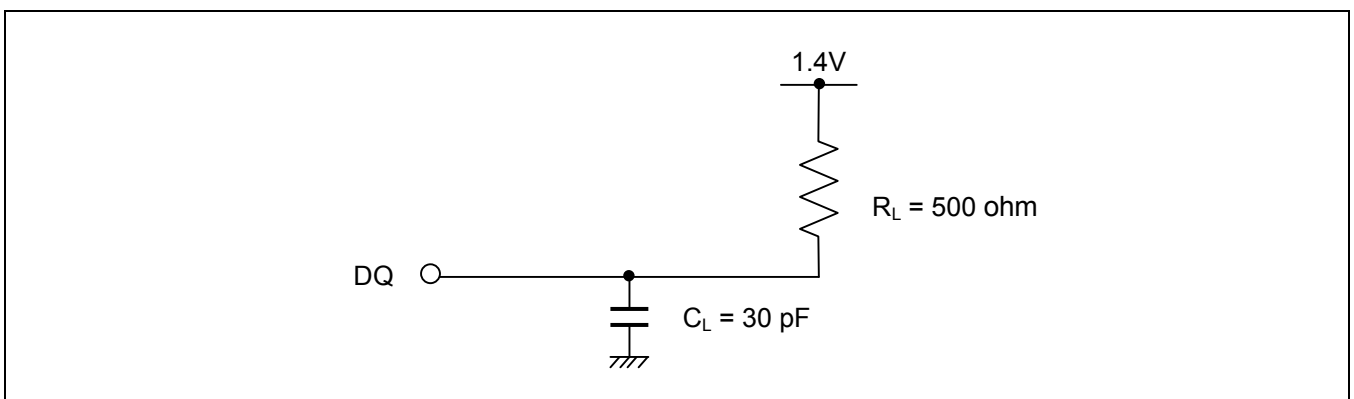
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C _{in}	-	-	10	pF	V _{in} =0V	1
Input / output capacitance	C _{I/O}	-	-	10	pF	V _{I/O} =0V	1

Note 1. Typical parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions (V_{cc} = 2.4V ~ 3.6V, Ta = -40 ~ +85°C)

- Input pulse levels: V_{IL} = 0.4V, V_{IH} = 2.4V (V_{cc} = 2.7V ~ 3.6 V)
V_{IL} = 0.4V, V_{IH} = 2.2V (V_{cc} = 2.4V ~ 2.7 V)
- Input rise and fall times: 5ns
- Input and output timing reference level: 1.4V
- Output load: See figures (Including scope and jig)



Read cycle

Parameter	Symbol	R1LV0816ASB-5SI (Note 0)		R1LV0816ASB-7SI		Unit	Note
		Min.	Max.	Min.	Max.		
Read cycle time	t_{RC}	55	-	70	-	ns	
Address access time	t_{AA}	-	55	-	70	ns	
Chip select access time	t_{ACS}	-	55	-	70	ns	
Output enable to output valid	t_{OE}	-	30	-	35	ns	
Output hold from address change	t_{OH}	10	-	10	-	ns	
LB#, UB# access time	t_{BA}	-	55	-	70	ns	
Chip select to output in low-Z	t_{CLZ}	10	-	10	-	ns	2,3
LB#, UB# enable to low-Z	t_{BLZ}	5	-	5	-	ns	2,3
Output enable to output in low-Z	t_{OLZ}	5	-	5	-	ns	2,3
Chip deselect to output in high-Z	t_{CHZ}	0	20	0	25	ns	1,2,3
LB#, UB# disable to high-Z	t_{BHZ}	0	20	0	25	ns	1,2,3
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1,2,3

Write Cycle

Parameter	Symbol	R1LV0816ASB-5SI (Note 0)		R1LV0816ASB-7SI		Unit	Note
		Min.	Max.	Min.	Max.		
Write cycle time	t_{WC}	55	-	70	-	ns	
Address valid to end of write	t_{AW}	50	-	65	-	ns	
Chip select to end of write	t_{CW}	50	-	65	-	ns	5
Write pulse width	t_{WP}	40	-	55	-	ns	4
LB#, UB# valid to end of write	t_{BW}	50	-	65	-	ns	
Address setup time	t_{AS}	0	-	0	-	ns	6
Write recovery time	t_{WR}	0	-	0	-	ns	7
Data to write time overlap	t_{DW}	25	-	35	-	ns	
Data hold from write time	t_{DH}	0	-	0	-	ns	
Output enable from end of write	t_{OW}	5	-	5	-	ns	2
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1,2
Write to output in high-Z	t_{WHZ}	0	20	0	25	ns	1,2

Note 0. If Vcc is 2.4-2.7V, parameters of R1LV0816ASB-7SI (70ns) are applied.

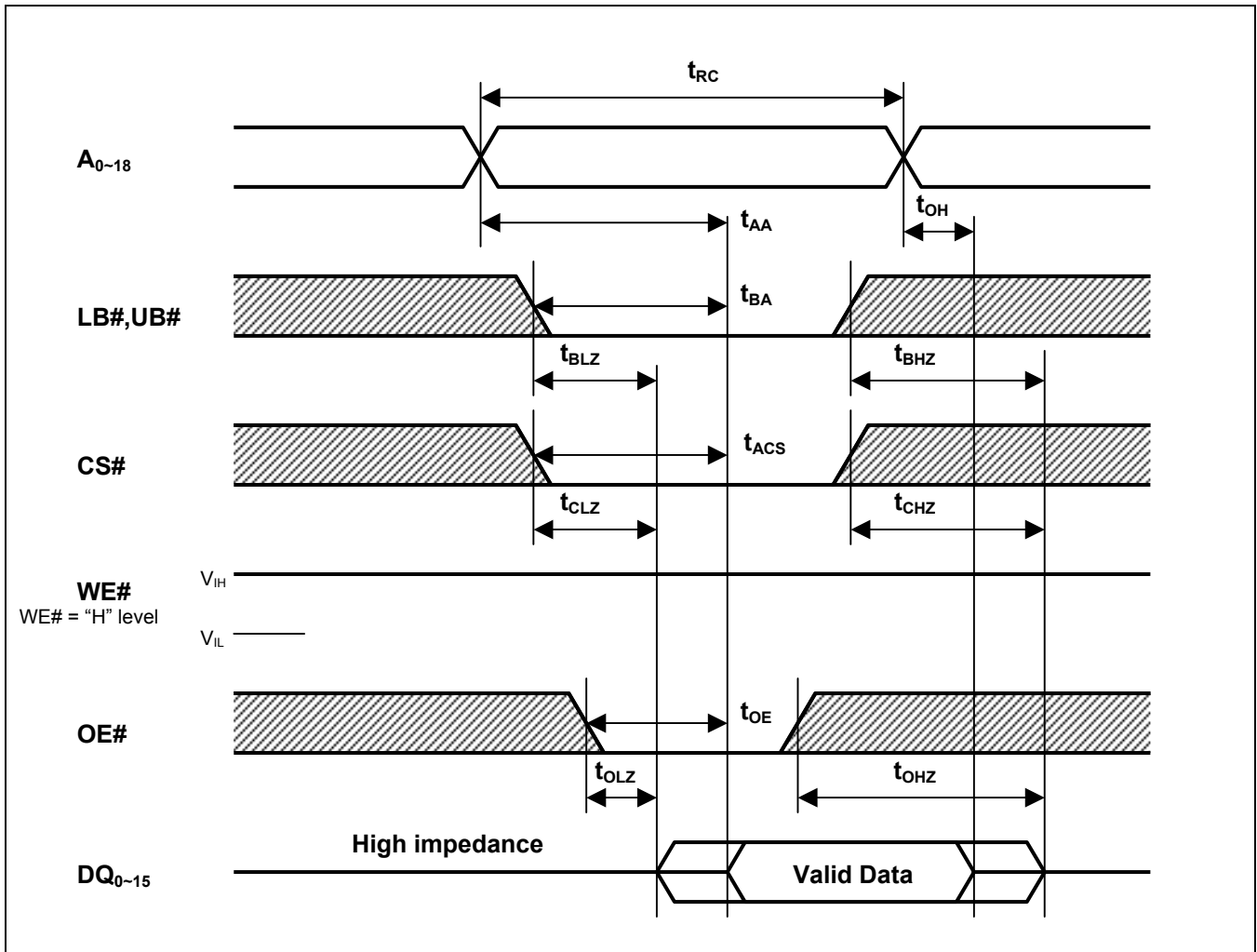
- t_{CHZ} , t_{OHZ} , t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
- Typical parameter is sampled and not 100% tested.
- At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for given device and from device to device.
- A write occurs during the overlap of a low CS#, a low WE# and a low LB# or low UB#.

A write begins at the latest transitions among CS# going low, WE# going low and LB# going low or UB# going low.

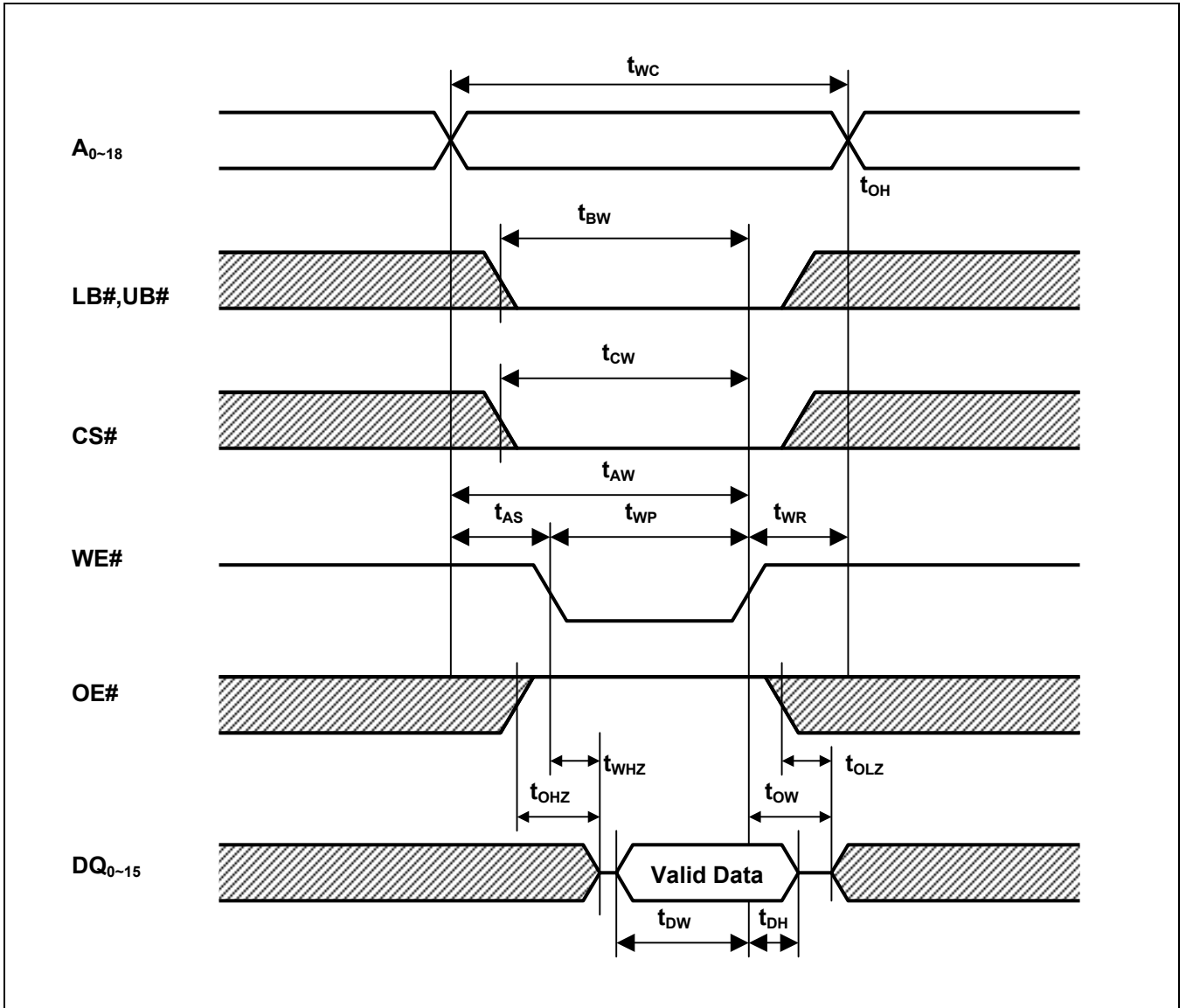
A write ends at the earliest transitions among CS# going high, WE# going high and LB# going high or UB# going high. t_{WP} is measured from the beginning of write to the end of write.
- t_{CW} is measured from the later of CS# going low to the end of write.
- t_{AS} is measured the address valid to the beginning of write.
- t_{WR} is measured from the earliest of CS# or WE# going high to the end of write cycle.

Timing Waveforms

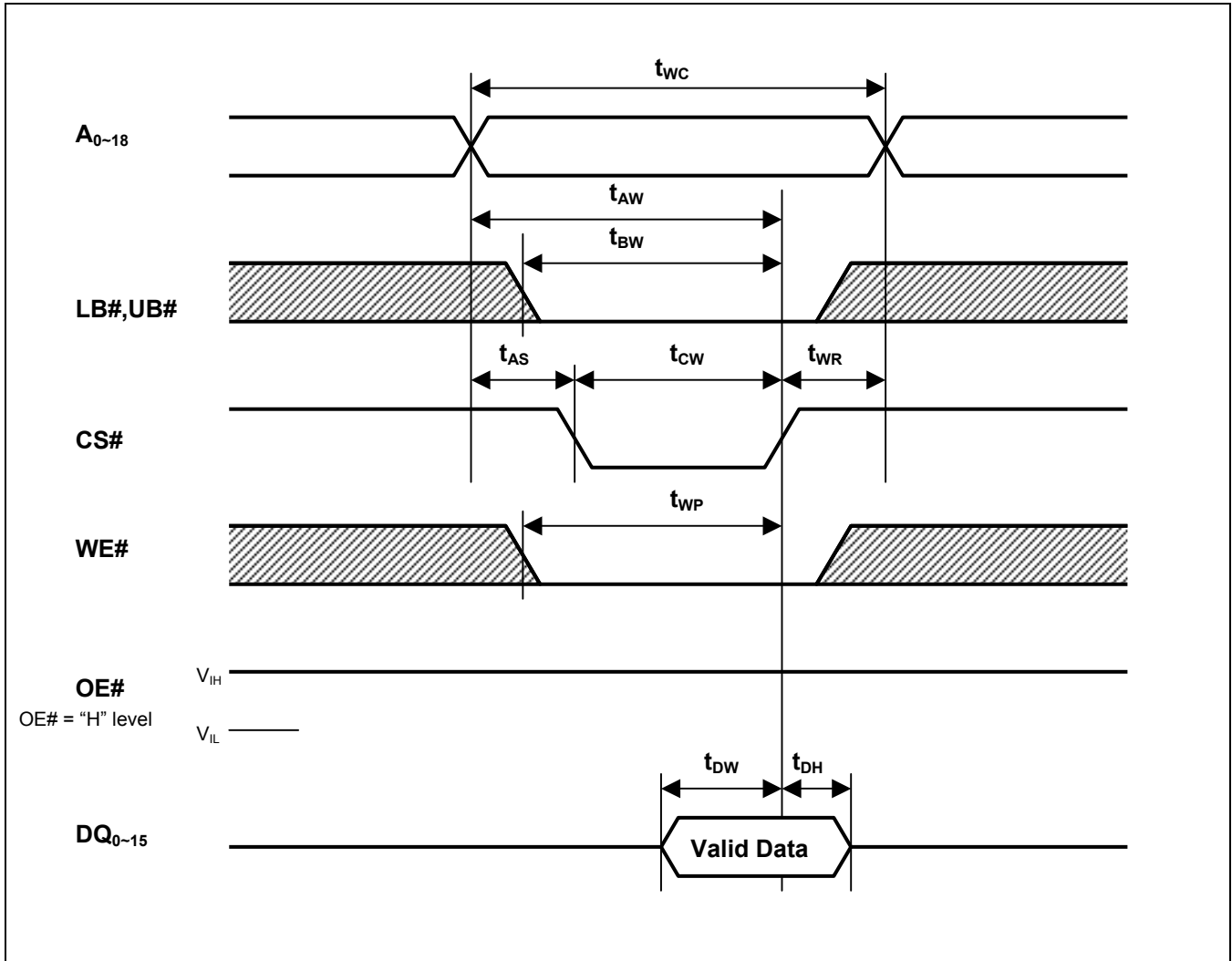
Read Cycle



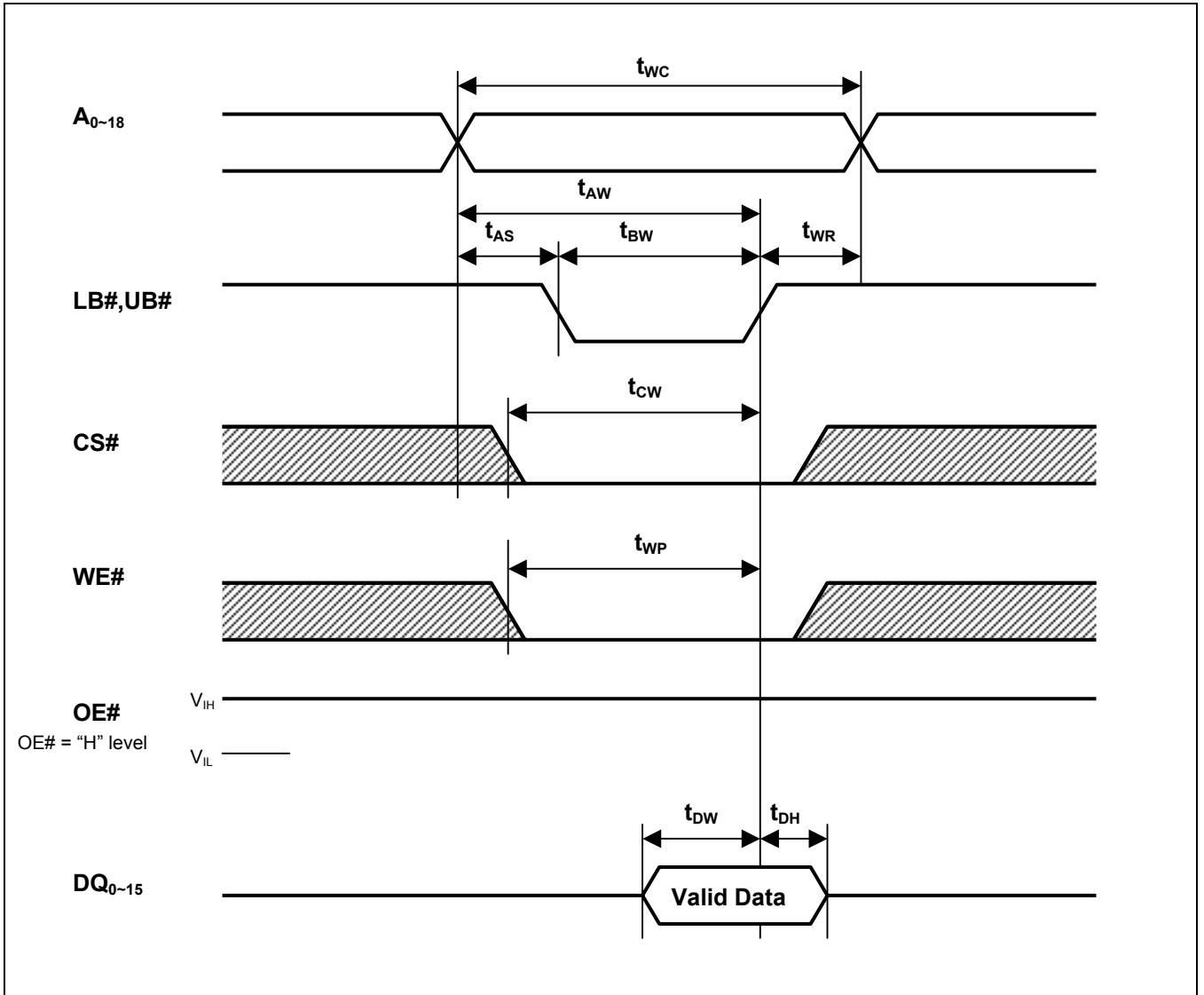
Write Cycle (1) (WE# CLOCK)



Write Cycle (2) (CS# CLOCK)



Write Cycle (3) (LB#, UB# CLOCK)



Data Retention Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions ^{*3}	
V_{CC} for data retention	V_{DR}	1.5	-	3.6	V	$V_{in} \geq 0V$ (1) $CS\# \geq V_{CC}-0.2V$, (2) $LB\# = UB\# \geq V_{CC}-0.2V$, $CS\# \leq 0.2V$,	
Data retention current	I_{CCDR}	-	1.2 ^{*1}	4	μA	$\sim +25^{\circ}C$	$V_{CC}=3.0V$, $V_{in} \geq 0V$ (1) $CS\# \geq V_{CC}-0.2V$ or (2) $LB\# = UB\# \geq V_{CC}-0.2V$, $CS\# \leq 0.2V$,
		-	3 ^{*2}	6	μA	$\sim +40^{\circ}C$	
		-	-	15	μA	$\sim +70^{\circ}C$	
		-	-	20	μA	$\sim +85^{\circ}C$	
Chip select to data retention time	t_{CDR}	0	-	-	ns	See retention waveform.	
Operation recovery time	t_R	5	-	-	ms		

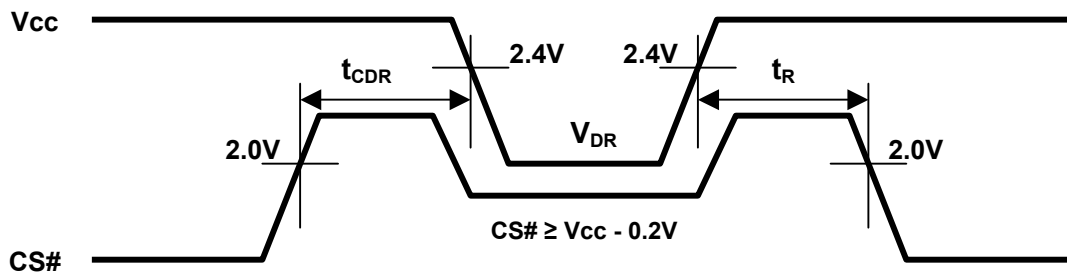
Note 1. Typical parameter indicates the value for the center of distribution at 3.0V($T_a=+25^{\circ}C$), and not 100% tested.

2. Typical parameter indicates the value for the center of distribution at 3.0V($T_a=+40^{\circ}C$), and not 100% tested.

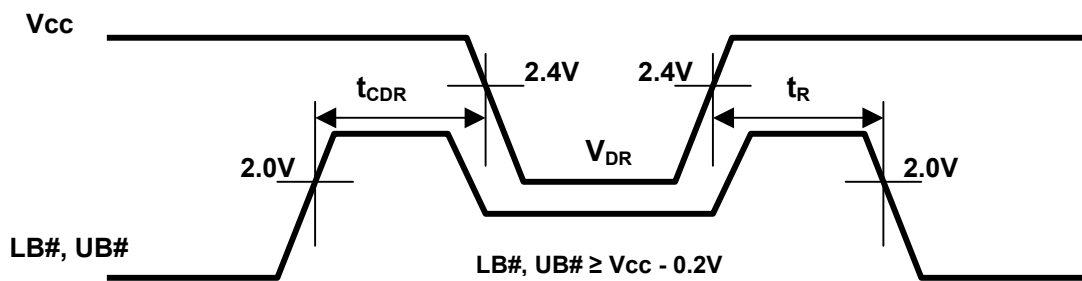
3. $CS\#$ controls address buffer, $WE\#$ buffer, $OE\#$ buffer, $LB\#$, $UB\#$ buffer and Din buffer. If $CS\#$ controls data retention mode, V_{in} levels (address, $WE\#$, $OE\#$, $LB\#$, $UB\#$, DQ) can be in the high impedance state.

Data Retention Timing Waveforms

(1) CS# controlled



(2) LB#, UB# controlled



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